

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	417	(memory near cell near storage) near15 (voltage or current)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/27 12:24	
2	BRS	L2	8	(memory near cell near storage) near15 (voltage or current) near15 (resistan\$3)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/27 12:26	
3	BRS	L3	151826	(voltage) near10 (resistanc\$3)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/27 12:27	
4	BRS	L4	13525	(voltage) near10 (resistanc\$3) near25 (electrode\$1)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/27 12:28	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	543	(voltage) near10 (resistanc\$3) near25 (electrode\$1) near25 (metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/27 12:28	
6	BRS	L6	83	(voltage) near10 (resistanc\$3) near25 (electrode\$1) near25 (metal) near25 (semiconduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/27 12:29	
7	BRS	L7	296	(chalcogenide) near25 (memory near cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/27 12:30	
8	BRS	L8	9	(chalcogenide) near25 (memory near cell near storage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/27 12:30	

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040052108 A1	THIN FILM MAGNETIC MEMORY DEVICE SUPPRESSING RESISTANCE OF TRANSISTORS PRESENT IN CURRENT PATH	365/173	22	20040318
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040042291 A1	Thin film magnetic memory device with magnetic tunnel junction	365/202	23	20040304
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030081450 A1	Thin film magnetic memory device for conducting data write operation by application of a magnetic field	365/158	48	20030501
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030027416 A1	METHOD OF FORMING INTEGRATED CIRCUITRY, METHOD OF FORMING MEMORY CIRCUITRY, AND METHOD OF FORMING RANDOM ACCESS MEMORY CIRCUITRY	438/618	12	20030206
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5726083 A	Process of fabricating dynamic random access memory device having storage capacitor low in contact resistance and small in leakage current through tantalum oxide film	438/210	22	19980310
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 2003016776 A	MEMORY CELL, STORAGE CIRCUIT BLOCK, DATA WRITE-IN METHOD, AND DATA READ-OUT METHOD		14	20030117
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 61177699 A	DYNAMIC TYPE SEMICONDUCTOR MEMORY DEVICE		NA	19860809
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 58218098 A	SEMICONDUCTOR MEMORY		5	19831219